

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

TPC6104

Notebook PC Applications

Portable Equipment Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 33 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 12 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10 \mu\text{A}$ (max) ($V_{DS} = -20 \text{ V}$)
- Enhancement mode: $V_{th} = -0.5$ to -1.2 V
($V_{DS} = -10 \text{ V}$, $I_D = -200 \mu\text{A}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-20	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-20	V
Gate-source voltage	V_{GSS}	± 8	V
Drain current	DC (Note 1)	I_D	A
	Pulse (Note 1)	I_{DP}	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2a)	P_D	2.2	W
Drain power dissipation ($t = 5 \text{ s}$) (Note 2b)	P_D	0.7	W
Single pulse avalanche energy (Note 3)	E_{AS}	4.9	mJ
Avalanche current	I_{AR}	-2.75	A
Repetitive avalanche energy (Note 4)	E_{AR}	0.22	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

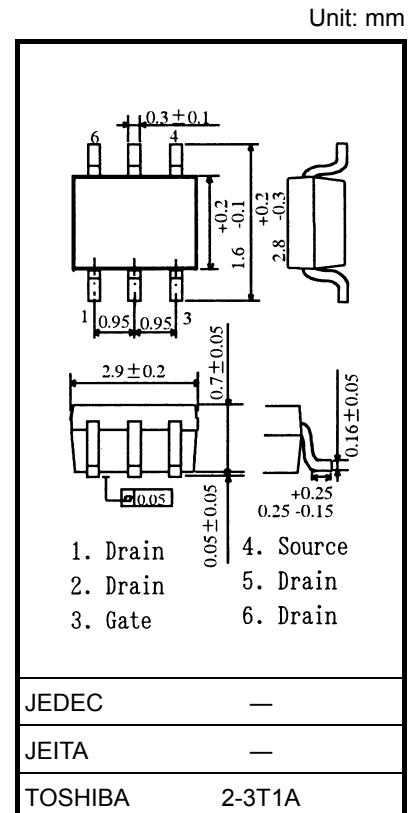
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

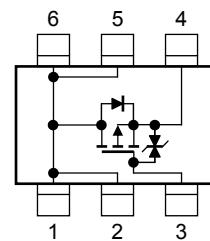
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient ($t = 5 \text{ s}$) (Note 2a)	$R_{th}(\text{ch-a})$	56.8	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ($t = 5 \text{ s}$) (Note 2b)	$R_{th}(\text{ch-a})$	178.5	$^\circ\text{C/W}$

Note: (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5): See the next page.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 0.011 g (typ.)

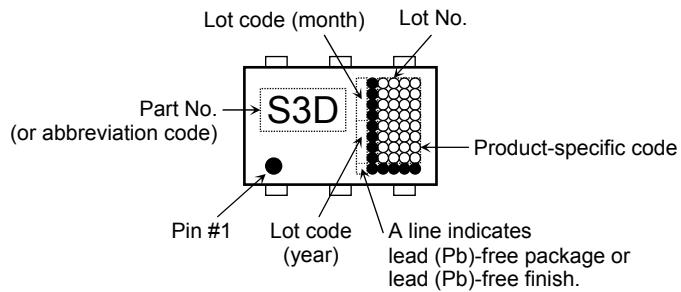
Circuit Configuration

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA	
Drain cut-off current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	μA	
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V	
	$V_{(\text{BR})\text{DSX}}$	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V}$	-12	—	—		
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_D = -200 \mu\text{A}$	-0.5	—	-1.2	V	
Drain-source ON resistance	$R_{DS} (\text{ON})$	$V_{GS} = -1.8 \text{ V}, I_D = -1.4 \text{ A}$	—	78	120	$\text{m}\Omega$	
	$R_{DS} (\text{ON})$	$V_{GS} = -2.5 \text{ V}, I_D = -2.8 \text{ A}$	—	49	60		
	$R_{DS} (\text{ON})$	$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$	—	33	40		
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.8 \text{ A}$	6	12	—	S	
Input capacitance	C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1430	—	pF	
Reverse transfer capacitance	C_{rss}		—	200	—		
Output capacitance	C_{oss}		—	240	—		
Switching time	Rise time	t_r	 V_{GS} : 0 V to -5 V	—	8.5	—	ns
	Turn-on time	t_{on}		—	15	—	
	Fall time	t_f		—	20	—	
	Turn-off time	t_{off}		—	66	—	
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -16 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -5.5 \text{ A}$	—	19	—	nC	
Gate-source charge	Q_{gs}		—	14	—		
Gate-drain ("miller") charge	Q_{gd}		—	5	—		

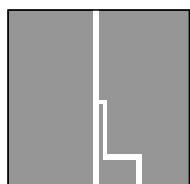
Source-Drain Ratings and Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	I_{DRP}	—	—	—	-22	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -5.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

Marking (Note 5)

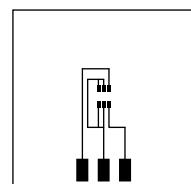
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) ($t = 5$ s)
(b) Device mounted on a glass-epoxy board (b) ($t = 5$ s)



FR-4
25.4 × 25.4 × 0.8
Unit: (mm)

(a)



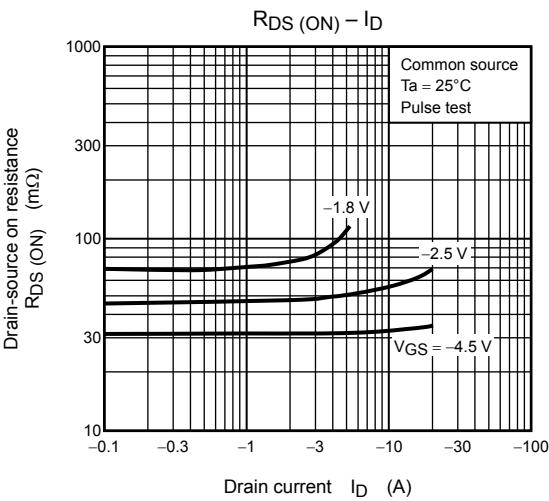
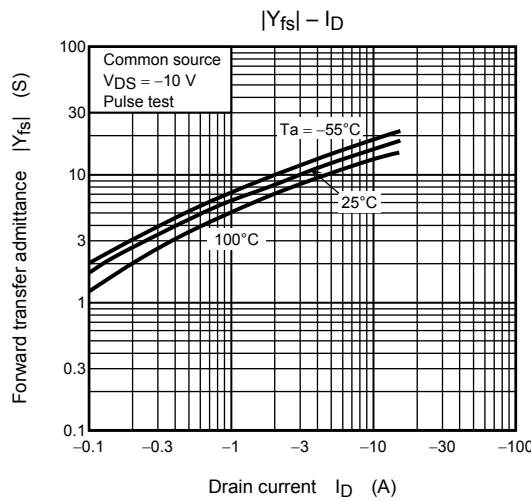
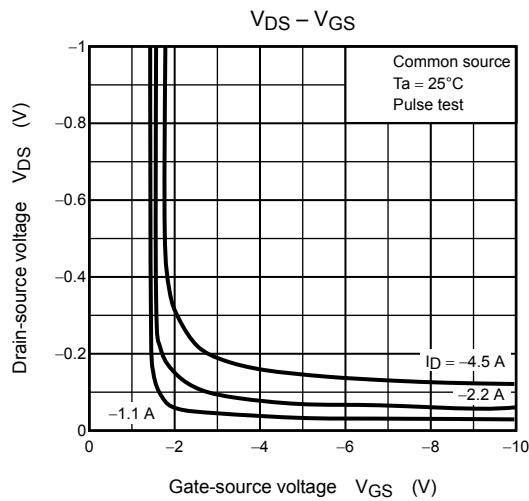
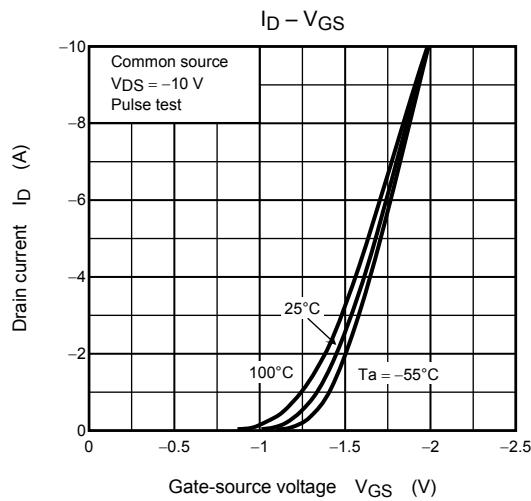
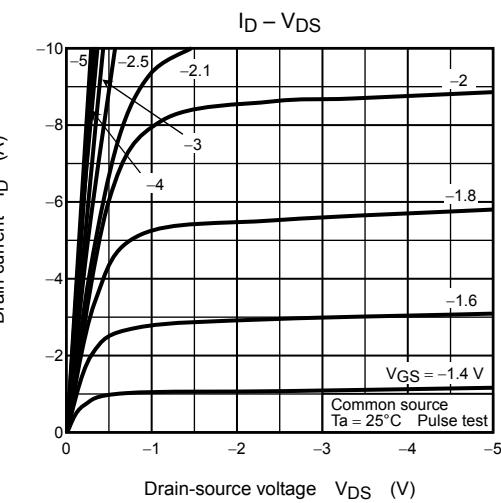
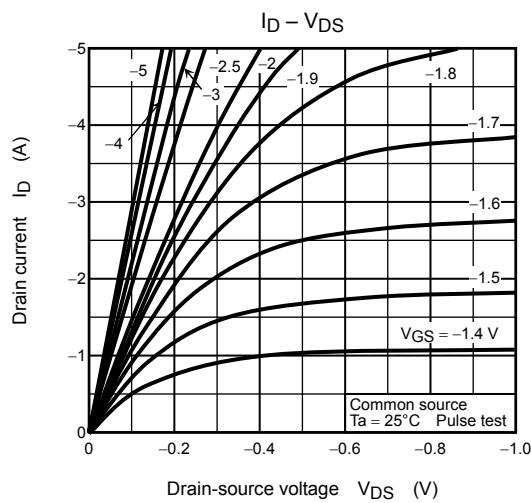
FR-4
25.4 × 25.4 × 0.8
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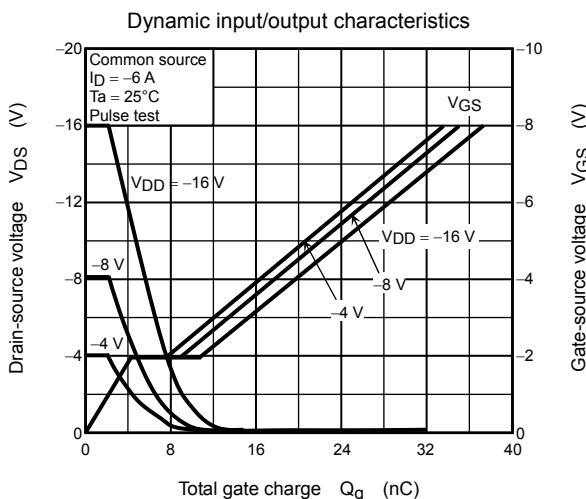
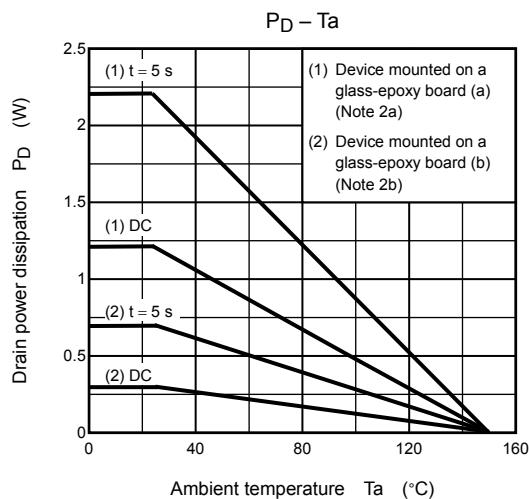
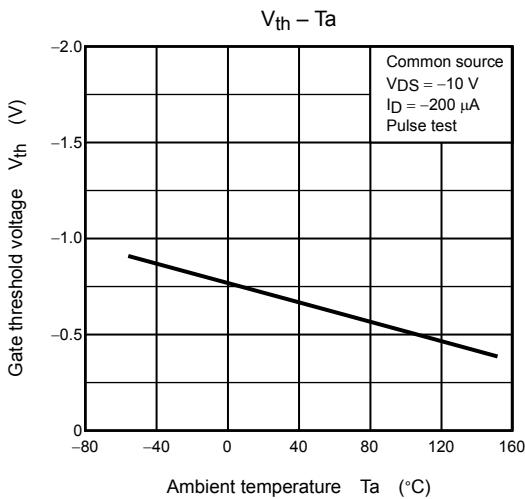
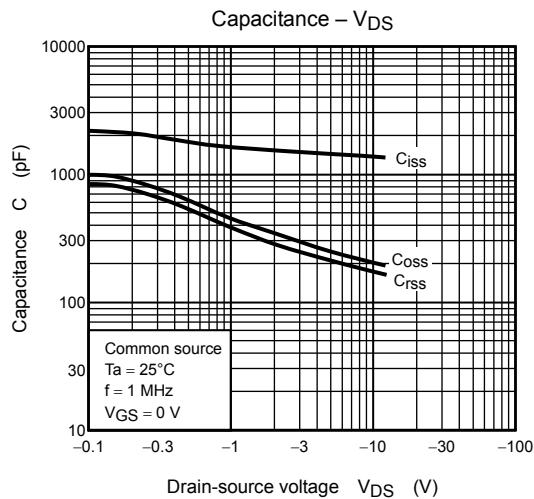
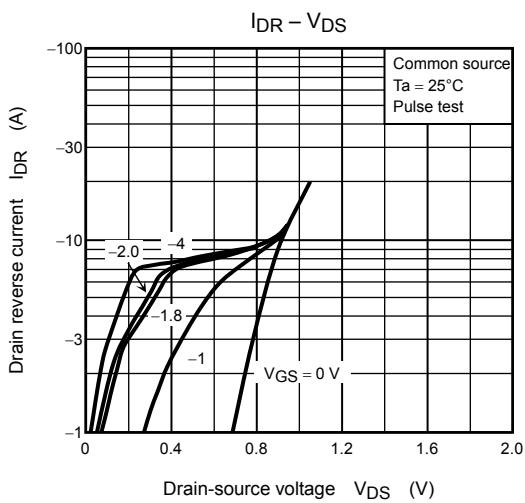
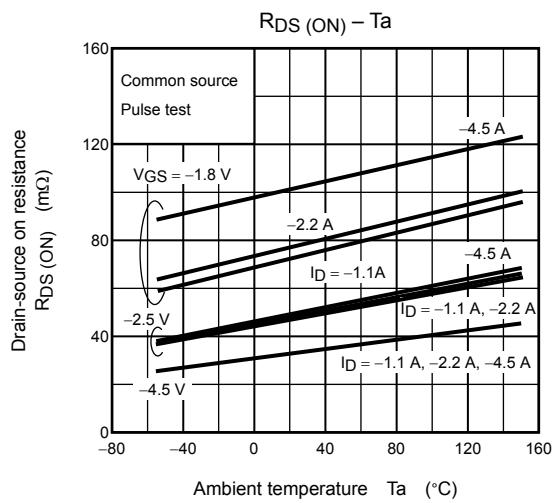
(b)

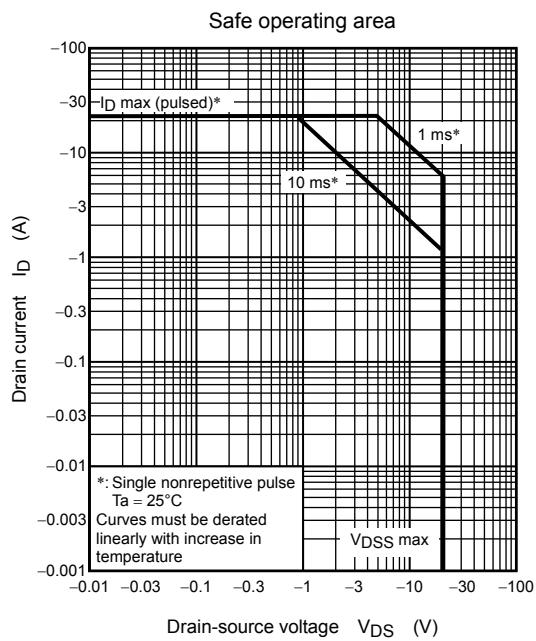
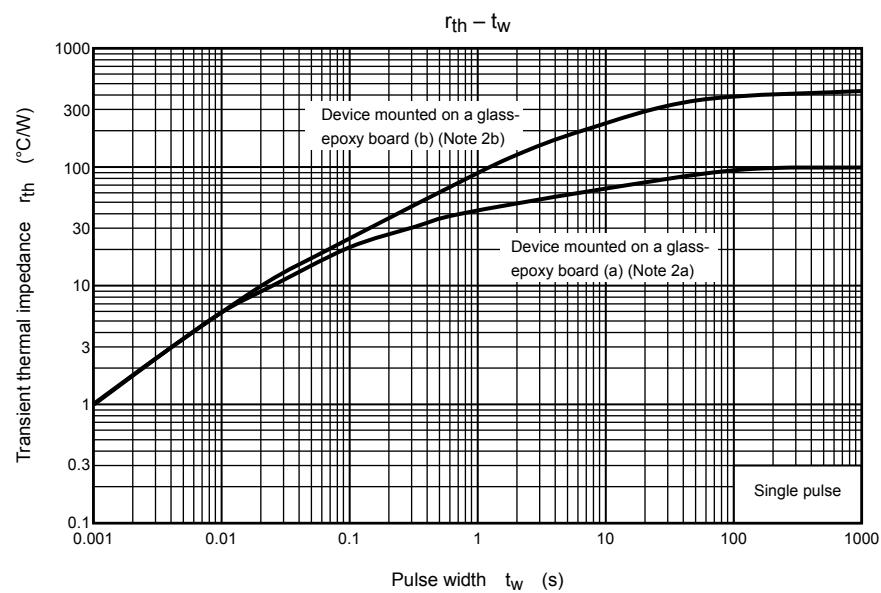
Note 3: $V_{DD} = -16$ V, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.5$ mH, $R_G = 25 \Omega$, $I_{AR} = -2.75$ A

Note 4: Repetitive rating::pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.







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20070701-EN

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
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